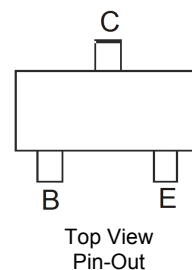
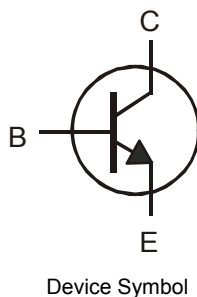


50V NPN SMALL SIGNAL SURFACE MOUNT TRANSISTOR
Features

- Epitaxial Planar Die Construction
- Ideal for Medium Power Amplification and Switching
- **Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

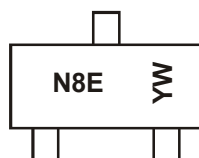
Mechanical Data

- Case: SOT23
- Case Material: molded plastic, "Green" molding compound
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.008 grams (approximate)


Ordering Information (Notes 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
2DC2412R-7	N8E	7	8	3,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>

Marking Information


N8E = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: Y = 2011)
 M = Month (ex: 9 = September)

Date Code Key

Year	2010	2011	2012	2013	2014	2015	2016	2017
Code	X	Y	Z	A	B	C	D	E

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

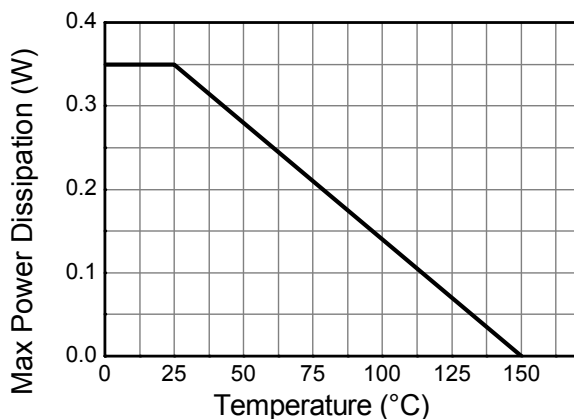
Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	60	V
Collector-Emitter Voltage	V _{CEO}	50	V
Emitter-Base Voltage	V _{EBO}	7.0	V
Continuous Collector Current	I _C	150	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

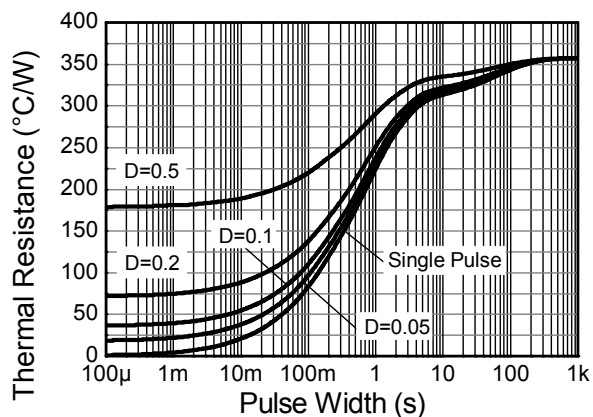
Characteristic	Symbol	Value	Unit
Power Dissipation	P _D	310	mW
		350	
Thermal Resistance, Junction to Ambient	R _{θJA}	403	°C/W
		357	
Thermal Resistance, Junction to Leads	R _{θJL}	350	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

- Notes:
5. For the device mounted on minimum recommended pad layout FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
 6. For the device mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
 7. Thermal resistance from junction to solder-point (at the end of the leads).

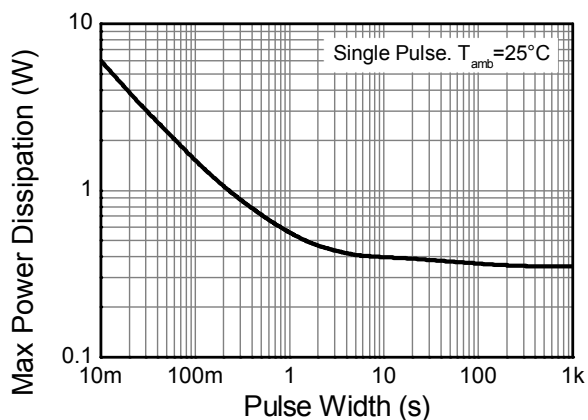
Thermal Characteristics



Derating Curve



Transient Thermal Impedance



Pulse Power Dissipation

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV _{CBO}	60	—	—	V	I _C = 100μA, I _E = 0
Collector-Emitter Breakdown Voltage (Note 8)	BV _{CEO}	50	—	—	V	I _C = 10mA, I _B = 0
Emitter-Base Breakdown Voltage	BV _{EBO}	7.0	—	—	V	I _E = 100μA, I _C = 0
Collector Cutoff Current	I _{CBO}	—	—	100	nA	V _{CB} = 60V
Base Cutoff Current	I _{EBO}	—	—	100	nA	V _{EB} = 6.0V
ON CHARACTERISTICS (Note 8)						
DC Current Gain	h _{FE}	180	—	390	—	I _C = 1.0mA, V _{CE} = 6.0V
Collector-Emitter Saturation Voltage	V _{CE(sat)}	—	0.2	0.4	V	I _C = 50mA, I _B = 5.0mA
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C _{obo}	—	2.0	3.5	pF	V _{CB} = 5.0V, f = 1.0MHz, I _E = 0
Current Gain-Bandwidth Product	f _T	80	180	—	MHz	V _{CE} = 12V, I _C = 2mA, f = 100MHz

Note: 8. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

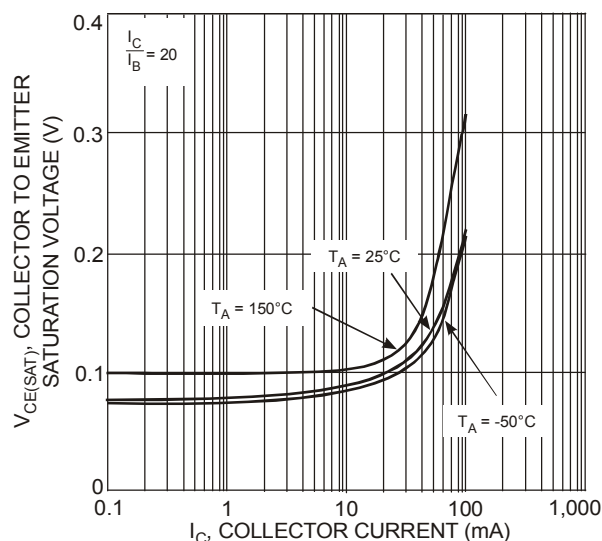


Figure 1 Collector Emitter Saturation Voltage vs. Collector Current

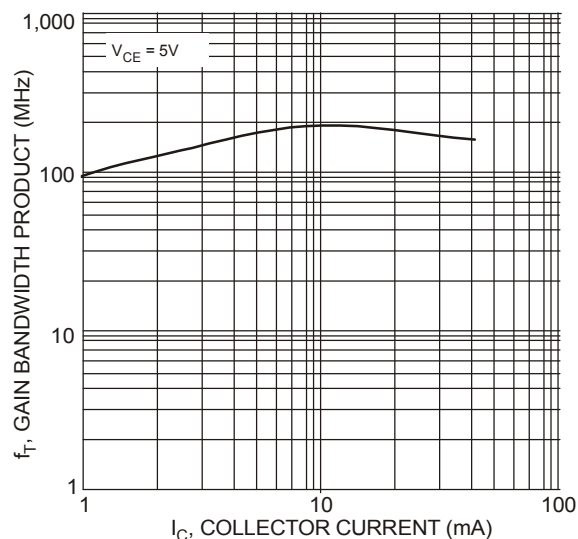


Figure 2 Gain Bandwidth Product vs. Collector Current

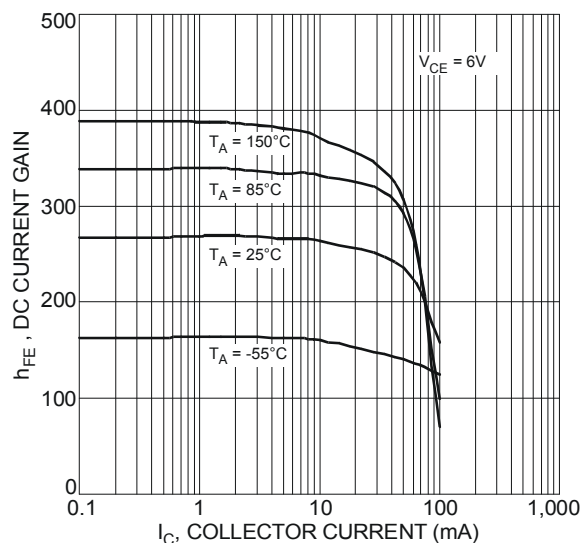
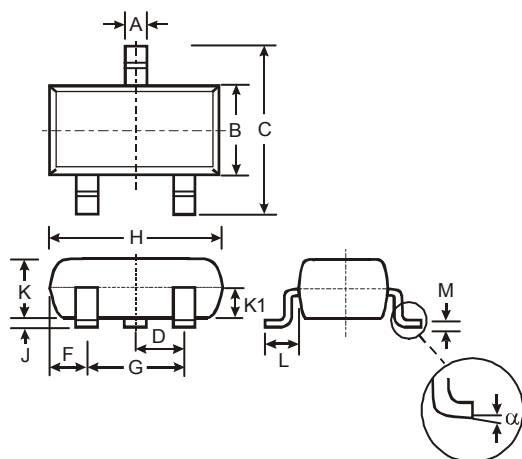


Figure 3 DC Current Gain vs. Collector Current

Package Outline Dimensions

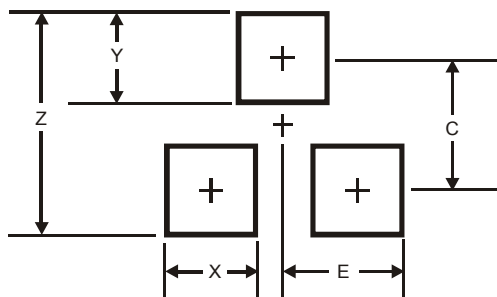
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.903	1.10	1.00
K1	-	-	0.400
L	0.45	0.61	0.55
M	0.085	0.18	0.11
α	0°	8°	-
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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